

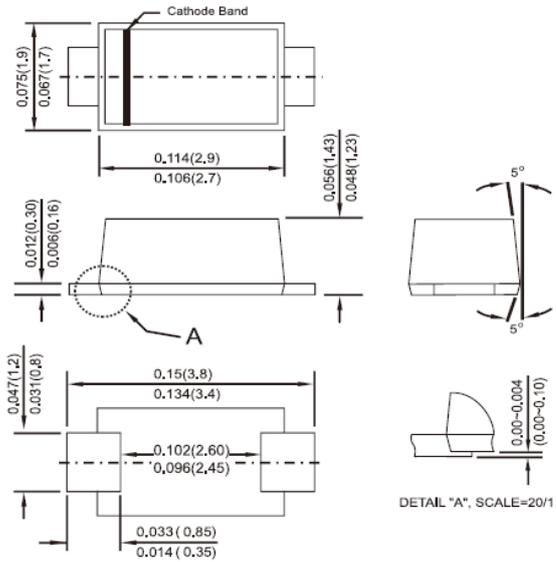


**Features**

- ✦ Silicon zener diodes
- ✦ Low profile surface-mount package
- ✦ Zener and surge current specification
- ✦ Low leakage current
- ✦ Excellent stability
- ✦ High temperature soldering guaranteed:  
260°C / 10 seconds/ .375", (9.5mm) lead length
- ✦ Green compound with suffix "G" on packing code & prefix "G" on datecode

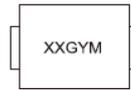
**Mechanical Data**

- ✦ Case: Sub SMA Plastic
- ✦ Terminals: Pure tin plated, lead free
- ✦ Packaging method: refer to package code
- ✦ Marking code: as table
- ✦ Weight: 0.0196 gram



**Dimensions in inches and (millimeters)**

**Marking Diagram**



- XX = Specific Device Code
- G = Green Compound
- Y = Year
- WW = Work Week

**Maximum Ratings and Electrical Characteristics**

Rating at 25 °C ambient temperature unless otherwise specified.

Type Number	Symbol	Value	Unit
Forward Voltage @ I <sub>F</sub> =0.2A	V <sub>F</sub>	1.2	Volts
Power Dissipation at TL=80°C TA=25 °C (Note 1)	P <sub>tot</sub>	2.3 1.0	Watts
Non-Repetitive Peak Pulse Power Dissipation 100us square pulse (Note 2)	P <sub>ZSM</sub>	300	Watts
Non-Repetitive Peak Pulse Power Dissipation 10/1000us waveform (BZD27C11P to BZD27C100P) (Note 2)	P <sub>RSM</sub>	150	Watts
Non-Repetitive Peak Pulse Power Dissipation 10/1000us waveform (BZD27C110P to BZD27C220P) (Note 2)	P <sub>RSM</sub>	100	Watts
Thermal Resistance Junction to Ambient Air (Note 1)	R <sub>θJA</sub>	180	°C/W
Thermal Resistance Junction to Lead	R <sub>θJL</sub>	30	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +175	°C

Note 1: Mounted on Cu-Pad size 5mm x 5mm (≥40um thick)

Note 2: T<sub>J</sub>=25°C Prior to Surge

## RATINGS AND CHARACTERISTIC CURVES (BZD27C SERIES)

FIG. 1 TYPICAL FORWARD CHARACTERISTICS

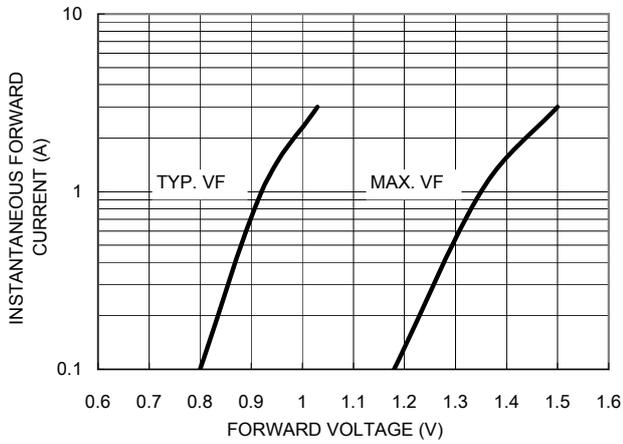


FIG. 2 TYP. DIODE CAPACITANCE vs REVERSE VOLTAGE

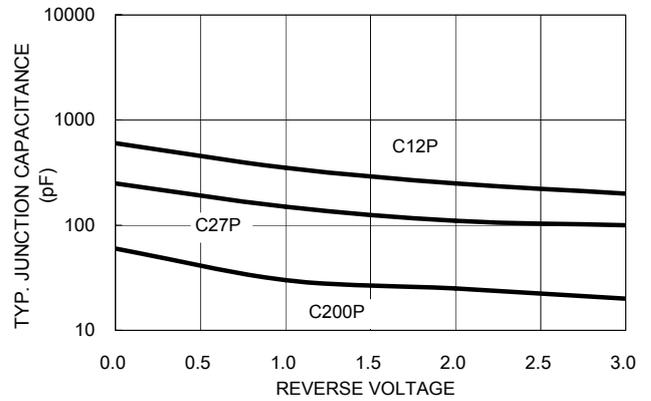


FIG.3 POWER DISSIPATION vs AMBIENT TEMPERATURE

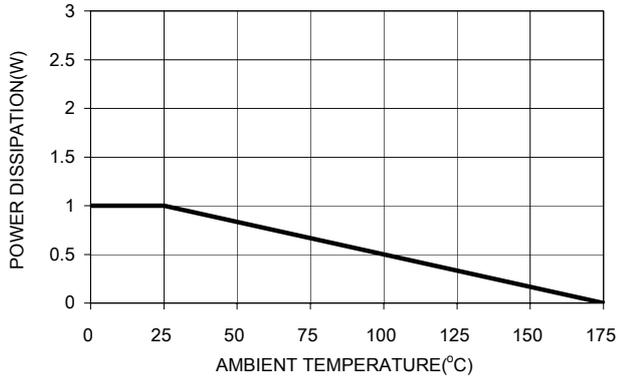
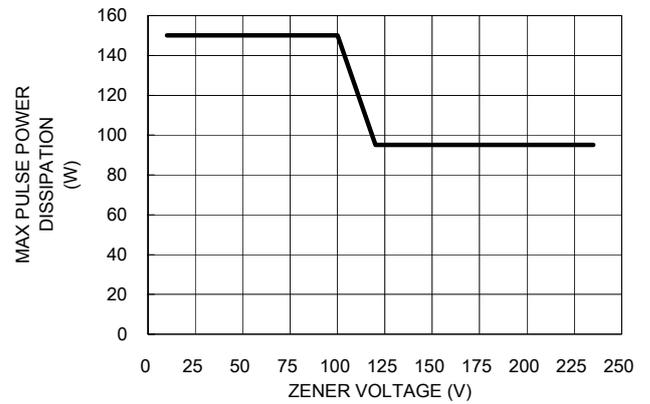


FIG. 4 MAXIMUM PULSE POWER DISSIPATION vs ZENER VOLTAGE



ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Device	Device Marking Code	Working Voltage (Note 1)		Differential Resistance		Temperature Coefficient		Test Current	Reverse Current@ Reverse Voltage	
		V <sub>Z</sub> @ I <sub>ZT</sub>		r <sub>diff</sub> @ I <sub>Z</sub>		ALPH <sub>Z</sub> @ I <sub>Z</sub>			I <sub>R</sub>	V <sub>R</sub>
		V		Ω		% / °C		mA	μA	V
		Min.	Max	typ	Max.	Min.	Max		Max.	
BZD27C11P	E2	10.4	11.6	4	7	0.05	0.10	50	4	8.2
BZD27C12P	E3	11.4	12.7	4	7	0.05	0.10	50	3	9.1
BZD27C13P	E4	12.4	14.1	5	10	0.05	0.10	50	2	10
BZD27C15P	E5	13.8	15.6	5	10	0.05	0.10	25	1	11
BZD27C16P	E6	15.3	17.1	6	15	0.06	0.11	25	1	12
BZD27C18P	E7	16.8	19.1	6	15	0.06	0.11	25	1	13
BZD27C24P	F0	22.8	25.6	7	15	0.06	0.11	25	1	18
BZD27C27P	F1	25.1	28.9	7	15	0.06	0.11	25	1	20
BZD27C30P	F2	28	32	8	15	0.06	0.11	25	1	22
BZD27C33P	F3	31	35	8	15	0.06	0.11	25	1	24
BZD27C36P	F4	34	38	21	40	0.06	0.11	10	1	27
BZD27C39P	F5	37	41	21	40	0.06	0.11	10	1	30
BZD27C43P	F6	40	46	24	45	0.07	0.12	10	1	33
BZD27C47P	F7	44	50	24	45	0.07	0.12	10	1	36
BZD27C51P	F8	48	54	25	60	0.07	0.12	10	1	39
BZD27C62P	G0	58	66	25	80	0.08	0.13	10	1	47
BZD27C68P	G1	64	72	25	80	0.08	0.13	10	1	51
BZD27C75P	G2	70	79	30	100	0.08	0.13	10	1	56
BZD27C100P	G5	94	106	60	200	0.09	0.13	4	1	75
BZD27C120P	G7	114	127	150	300	0.09	0.13	4	1	91
BZD27C180P	H1	168	191	280	450	0.09	0.13	4	1	130
BZD27C200P	H2	188	212	350	750	0.09	0.13	4	1	150
BZD27C220P	H3	208	233	430	900	0.09	0.13	4	1	160

Notes: 1. Pulse test: tp ≤ 5ms.

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Device	Rev. Breakdown Voltage	Test Current	Temperature Coefficient		Clamping Voltage		Reverse Current@ Stand-Off Voltage	
	V(BR)@Itest	Itest	ALPHz@Itest		Vc	@IRSM (Note 1)	IR	@VWM
	V	mA	%°C		V	A	uA	V
	Min.		Min.	Max	Max.		Max.	
BZD27C11P	10.4	50	0.05	0.10	15.7	9.6	5	9.1
BZD27C12P	11.4	50	0.05	0.10	17	8.8	5	10
BZD27C13P	12.4	50	0.05	0.10	18.9	7.9	5	11
BZD27C15P	13.8	50	0.05	0.10	20.9	7.2	5	12
BZD27C16P	15.3	25	0.06	0.11	22.9	6.6	5	13
BZD27C18P	16.8	25	0.06	0.11	25.6	5.9	5	15
BZD27C24P	22.8	25	0.06	0.11	33.8	4.4	5	20
BZD27C27P	25.1	25	0.06	0.11	38.1	3.9	5	22
BZD27C30P	28	25	0.06	0.11	42.2	3.6	5	24
BZD27C33P	31	25	0.06	0.11	46.2	3.2	5	27
BZD27C36P	34	10	0.06	0.11	50.1	3	5	30
BZD27C39P	37	10	0.06	0.11	54.1	2.8	5	33
BZD27C43P	40	10	0.07	0.12	60.7	2.5	5	36
BZD27C47P	44	10	0.07	0.12	65.5	2.3	5	39
BZD27C51P	48	10	0.07	0.12	70.8	2.1	5	43
BZD27C62P	58	10	0.08	0.13	86.5	1.7	5	51
BZD27C68P	64	10	0.08	0.13	94.4	1.6	5	56
BZD27C75P	70	10	0.08	0.13	103.5	1.5	5	62
BZD27C100P	94	5	0.09	0.13	139	1.1	5	82
BZD27C120P	114	5	0.09	0.13	152	0.65	5	100
BZD27C180P	168	5	0.09	0.13	229	0.43	5	150
BZD27C200P	188	5	0.09	0.13	254	0.39	5	160
BZD27C220P	208	5	0.09	0.13	279	0.35	5	176

Notes: 1. Non-repetitive peak reverse current in accordance with "IEC 60-1, Section 8" (10/1000 us pulse)

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